



FORM PT-1449	SERIAL NO. 10/777,911	CASE NO. 12357-3
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)	FILING DATE February 11, 2004	GROUP ART UNIT 2815 Unassigned
APPLICANT(S): Shen et al.		

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
	A1	6,680,494	1/2004	GUTIERREZ-AITKEN ET AL.		
	A2	6,563,145	5/2003	CHANG ET AL.		

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO

EXAMINER INITIAL	OTHER ART - NON PATENT LITERATURE DOCUMENTS <small>(Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)</small>	
	A3	Hong Wang and Geok Ing Ng, "Investigation of the Degradation of InGaAs/InP Double HBTs Under Reverse Base-Collector Bias Stress," Vol. 48, No. 11, IEEE Transactions on Electron Devices, pp. 2647-2654, November 2001.
	A4	Hin-Fai Chau, Dimitris Pavlidis, Juntao Hu, and Kazutaka Tomizawa, "Breakdown-Speed Considerations in InP/InGaAs Single- and Double-Heterostructure Bipolar Transistors," Vol. 40, No. 1, IEEE Transactions on Electron Devices, pp. 2-8, January 1993.
	A5	Peter M. Asbeck, Frank Mau-Chung Chang, Keh-Chung Wang, Gerard J. Sullivan, and Derek T. Cheung, "GaAs-Based Heterojunction Bipolar Transistors for Very High Performance Electronic Circuits," Vol. 81, No. 12, Proceedings of the IEEE, pp. 1709-1726, December 1993.

EXAMINER 	DATE CONSIDERED 1/06
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.